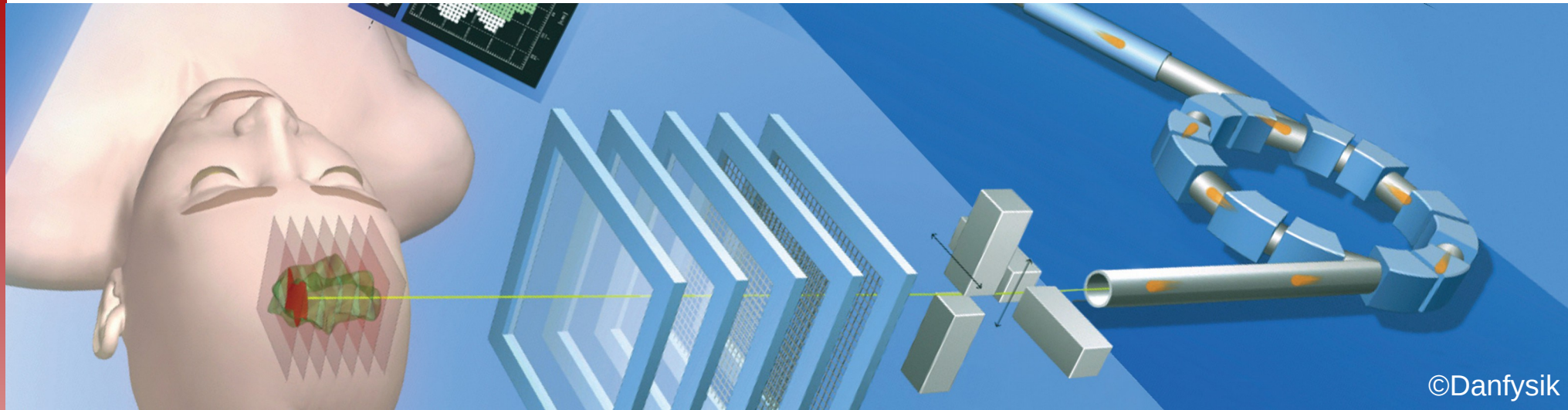


CMOS applications for charged particle detection (nuclear/mass spectroscopy/medical)



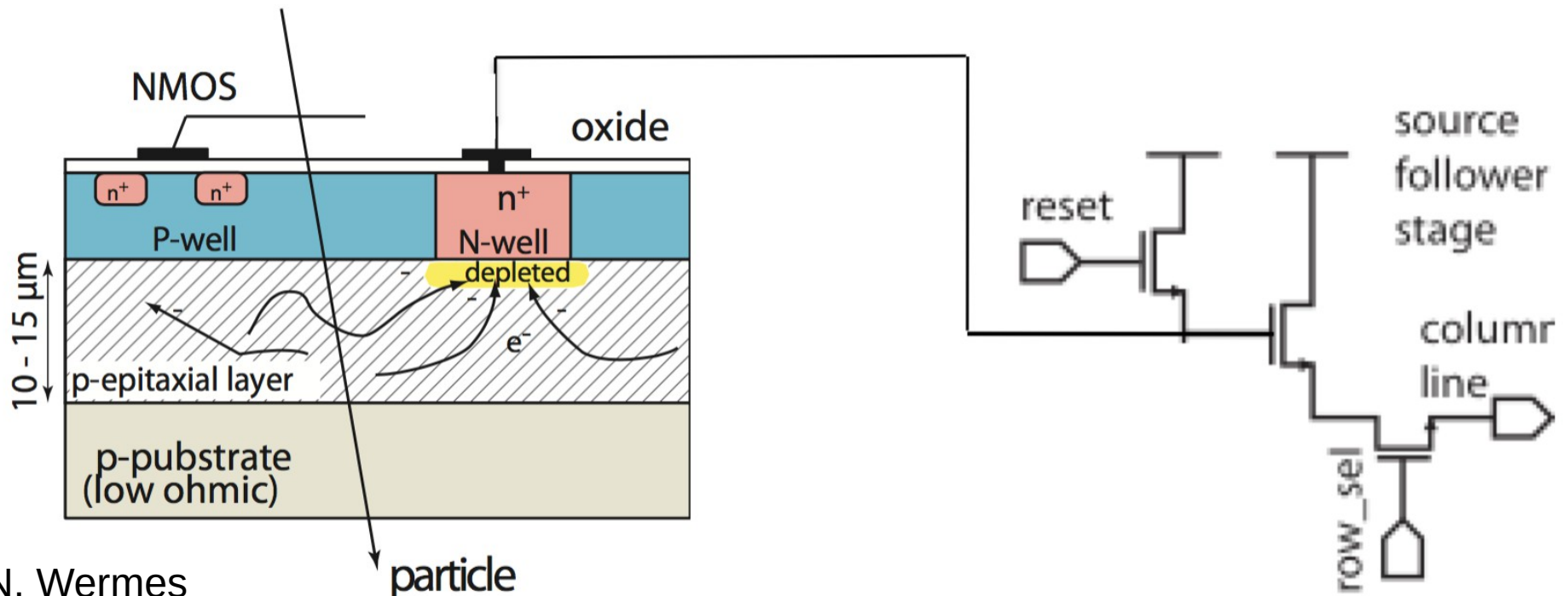
Daniel Muenstermann

Scope of this talk

- I was asked to give an overview/a sample of potential applications for CMOS sensors beyond particle physics focussing on detection of charged particles
- Disclaimer: I am not an expert for most of the applications discussed
 - take my slides with a grain of salt
 - let me know if you spot any obvious mistakes
- There have already been dedicated particle sensors (often designated as monolithic active pixel sensors or “MAPS”) for a rather long time, but
 - these were usually relying on diffusion as means of charge collection
 - slow
 - fails already for comparatively low amounts of trapping from (bulk) radiation damage
- The same is (mostly) true for classical CMOS imaging sensors which enabled to have cameras in virtually all everyday gadgets like mobile phones
- I will try to point out potential applications of drift-based CMOS sensors

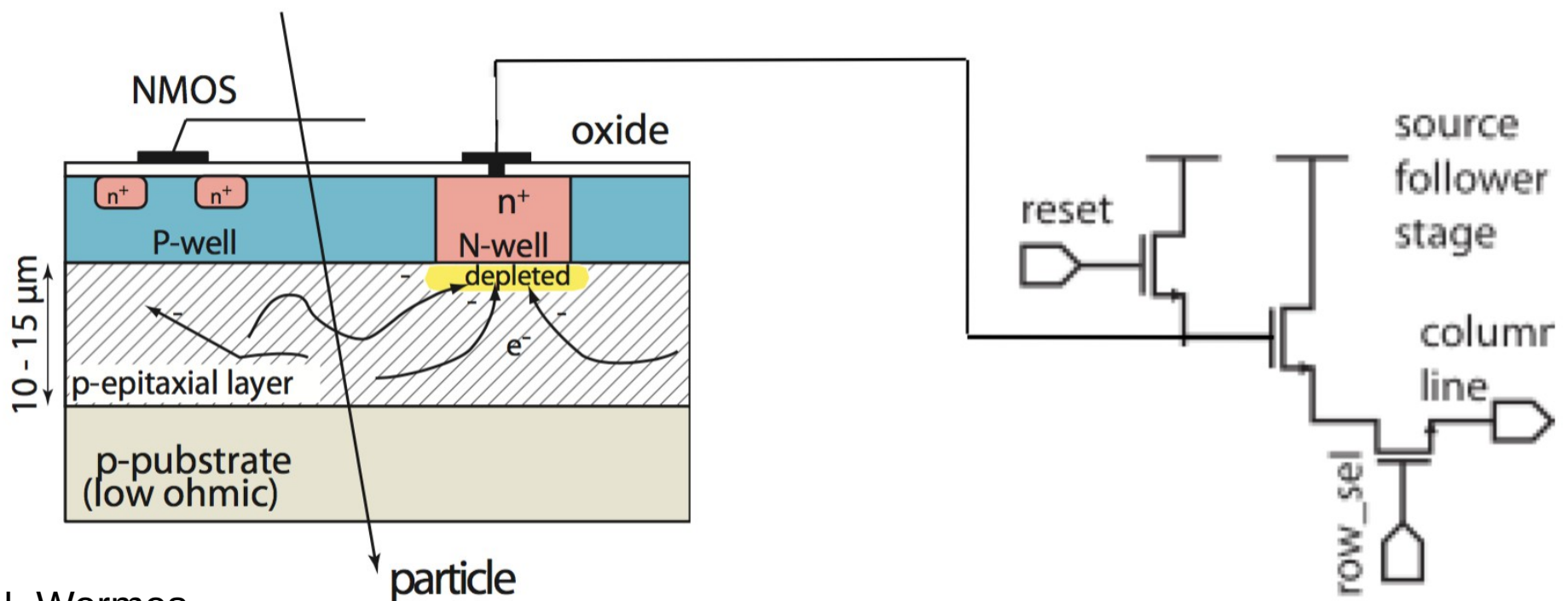
Charged particle detection in CMOS

- Main idea: electrons (or holes) survive long enough to reach collection electrodes
 - use high-grade silicon layer to accomplish → epi
 - rely on diffusion → slow, not rad-hard
- use built-in voltage at pn-junction to collect charge, use small capacitance of electrode to reach sufficient voltage levels
- classical readout scheme: 3/4/5 transistor, requires reset, does usually not account for leakage current, rolling shutter/sequential readout (slow)



Charged particle detection in CMOS

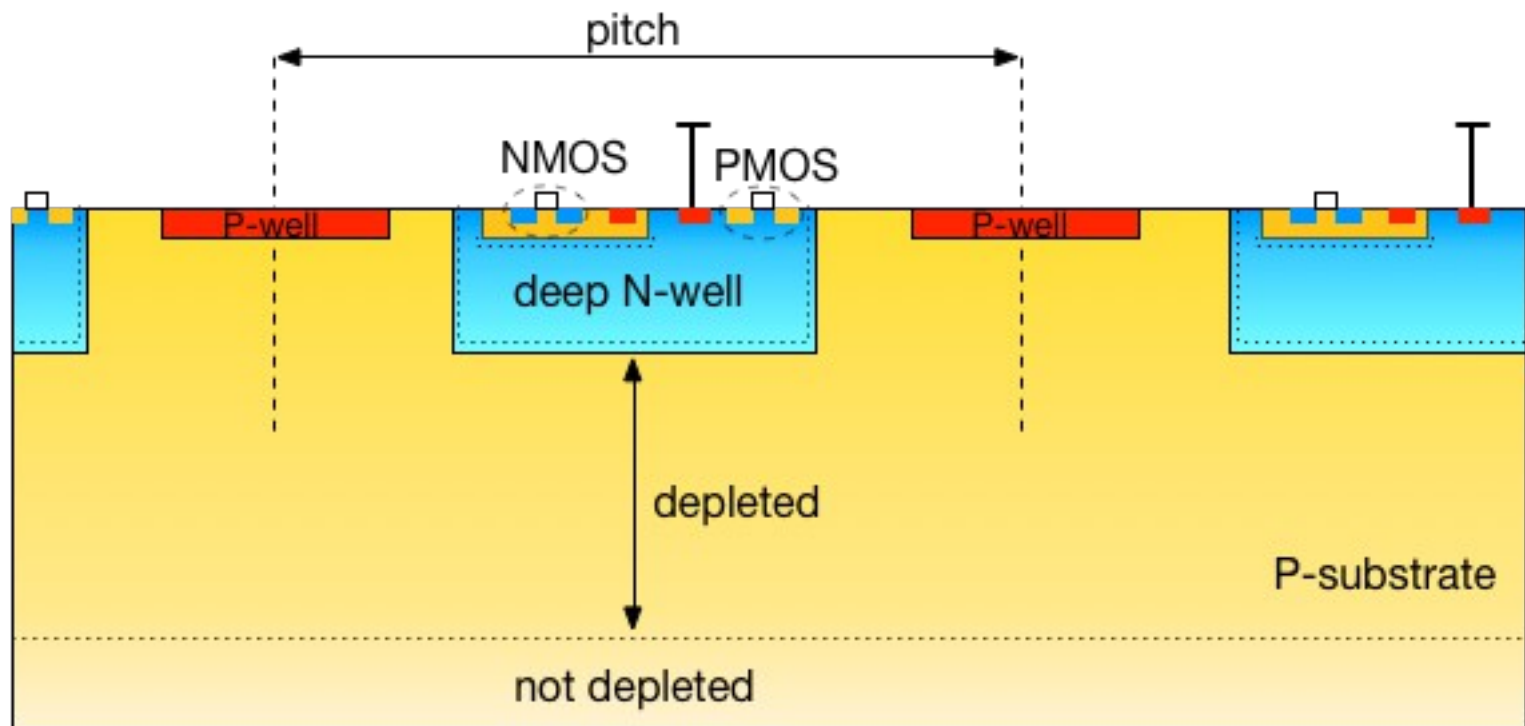
- Advantages of MAPS sensors
 - small pixel sizes possible
 - readout electronics mostly integrated in sensor
 - cost-efficient production
- Disadvantages of MAPS sensors
 - not radiation-tolerant
 - comparatively bad timing
 - depending on readout scheme: slow, inevitable dead-time, no self-trigger



N. Wermes

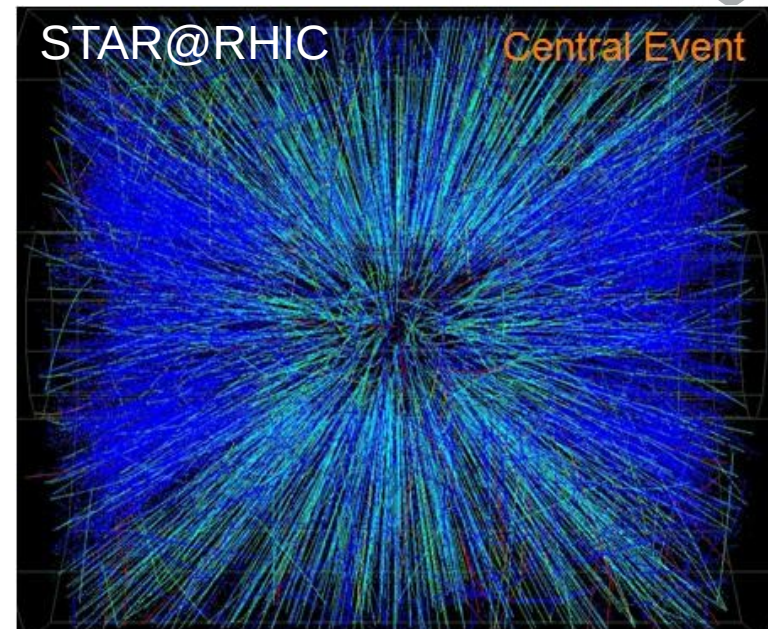
“Classical MAPS” → HV/HR-CMOS

- Apply bias voltage to bulk → rely on drift instead of diffusion
- Avoid charge collection on parasitic wells by shielding them inside a deep n-well
- Take care of inter-pixel isolation after irradiation by suitable techniques
- Often a rather classical charge-sensitive amplifier with leakage current compensation is used at the expense of larger pixels
- New applications opening up?

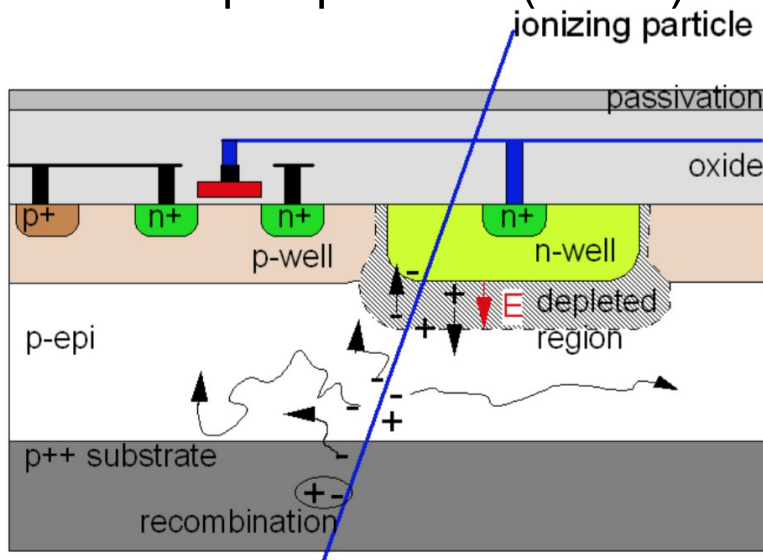


Nuclear Physics Applications

- Classical application: Particle tracking
 - not particle physics? → Similar, but still different
 - often large multiplicities
 - particle energies
 - Particle/Hadron/Nuclear physics?
- Examples:
 - STAR
 - Panda Luminosity Monitor



- STAR (→ Petra Riedler's talk)
 - AMS 350nm opto process (C350)



The STAR detector @ RHIC

Layer	Radius (cm)
SSD	$r = 22$
IST	$r = 14$
PXL	$r_2 = 8$
	$r_1 = 2.8$

HFT

3 G. Contin | gcontin@lbl.gov

Nuclear Physics Applications

- STAR
 - rather moderate radiation environment
 - material budget rather low
 - timing generous

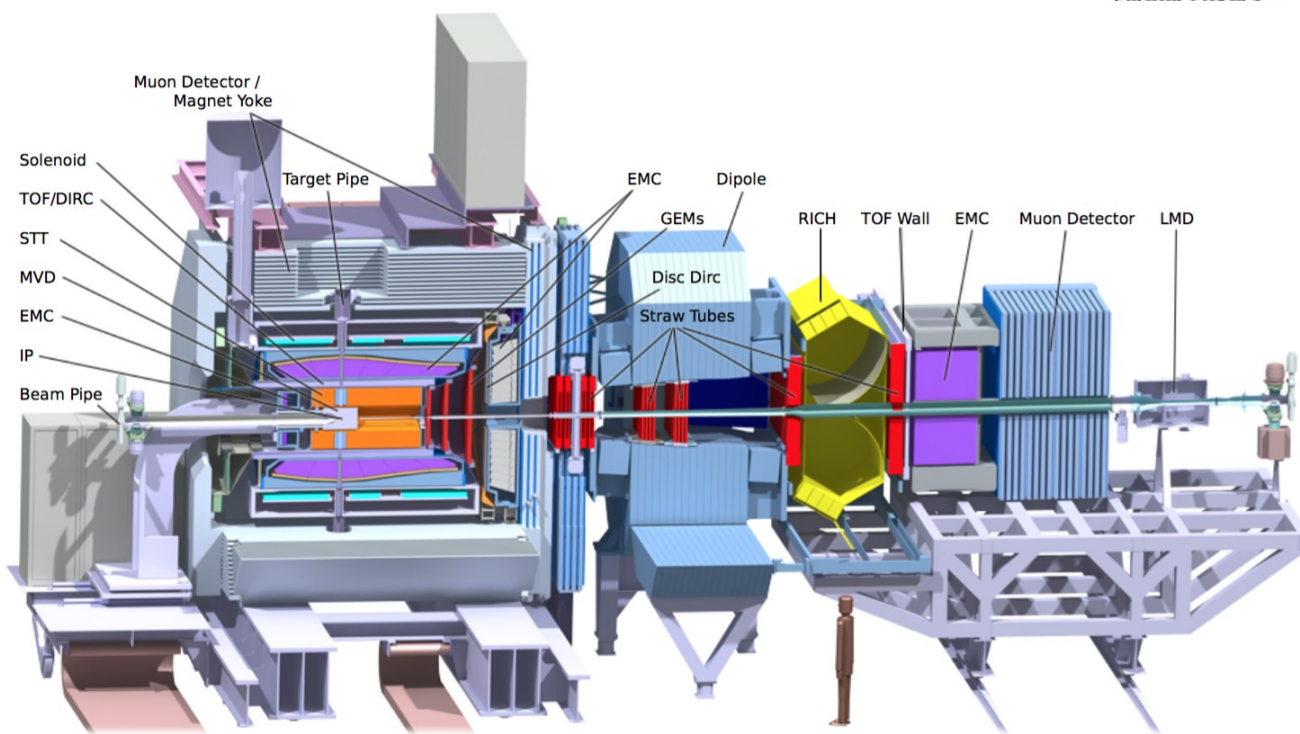
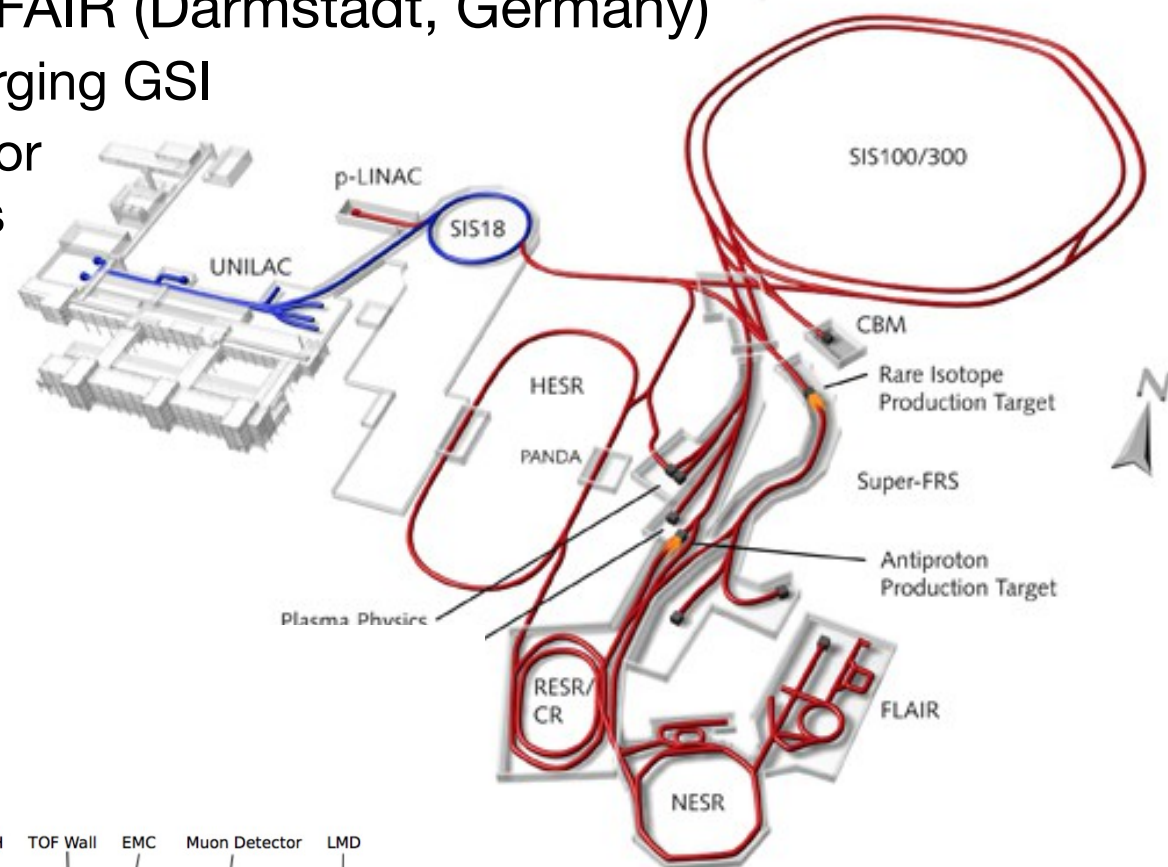
PXL Detector Design Parameters

DCA Pointing resolution	$(10 \oplus 24 \text{ GeV}/p\text{-c}) \mu\text{m}$
Layers	Layer 1 at 2.8 cm radius Layer 2 at 8 cm radius
Pixel size	$20.7 \mu\text{m} \times 20.7 \mu\text{m}$
Hit resolution	$3.7 \mu\text{m}$ ($6 \mu\text{m}$ geometric)
Position stability	$5 \mu\text{m}$ rms ($20 \mu\text{m}$ envelope)
Material budget first layer	$X/X_0 = 0.39\%$ (Al conductor cable)
Number of pixels	356 M
Integration time (affects pileup)	$185.6 \mu\text{s}$
Radiation environment	20 to 90 kRad / year $2 \cdot 10^{11}$ to 10^{12} IMeV n eq/cm ²
Rapid detector replacement	< 1 day

356 M pixels on $\sim 0.16 \text{ m}^2$ of Silicon

Nuclear Physics Applications

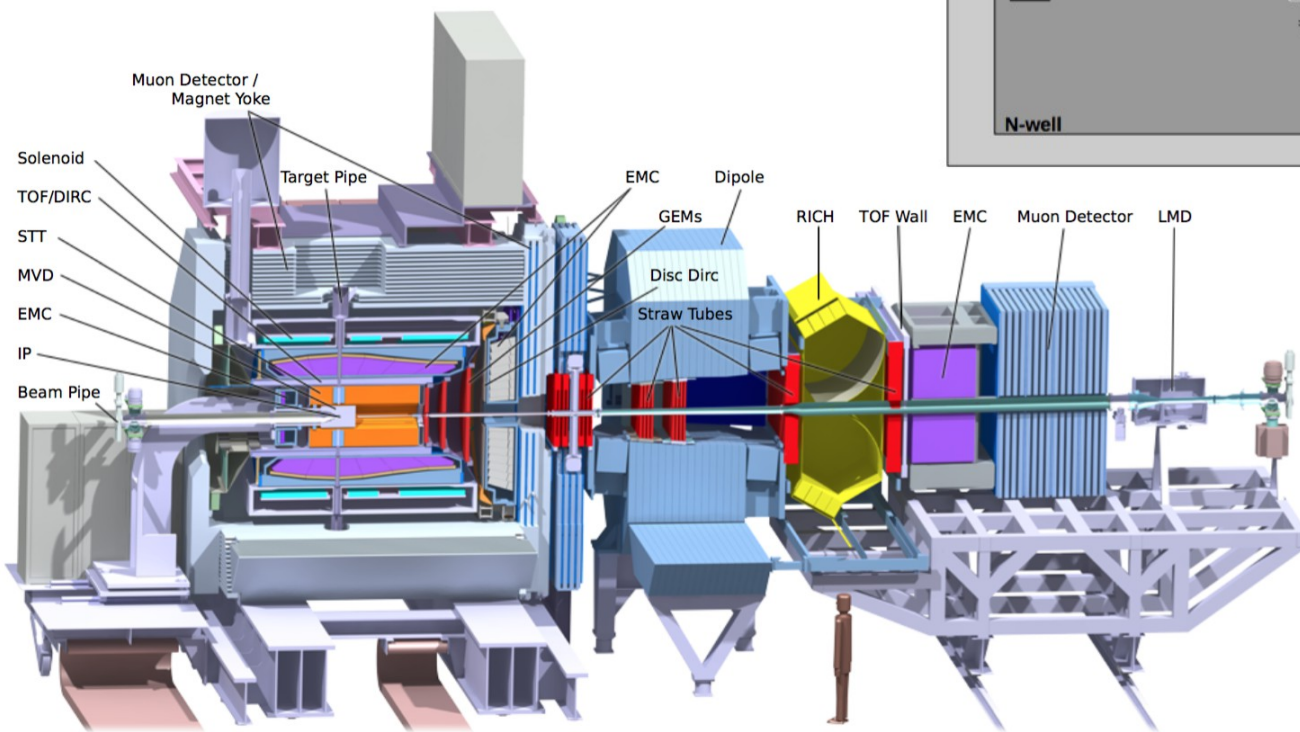
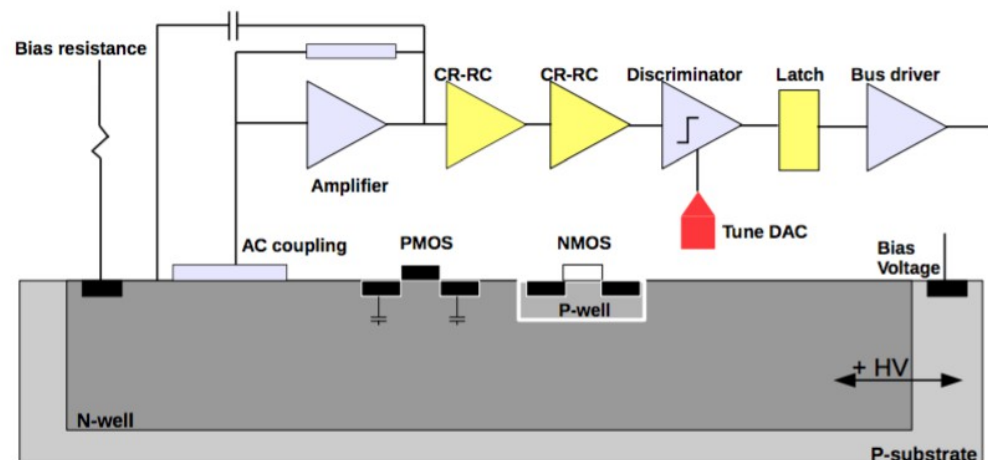
- Panda Luminosity Monitor @ FAIR (Darmstadt, Germany)
 - ongoing site construction enlarging GSI
 - Panda being a versatile detector for proton-antiproton collisions
 - hadron spectroscopy
 - nucleon structure
 - hadrons in matter
 - hypernuclei



Tobias Weber

Nuclear Physics Applications

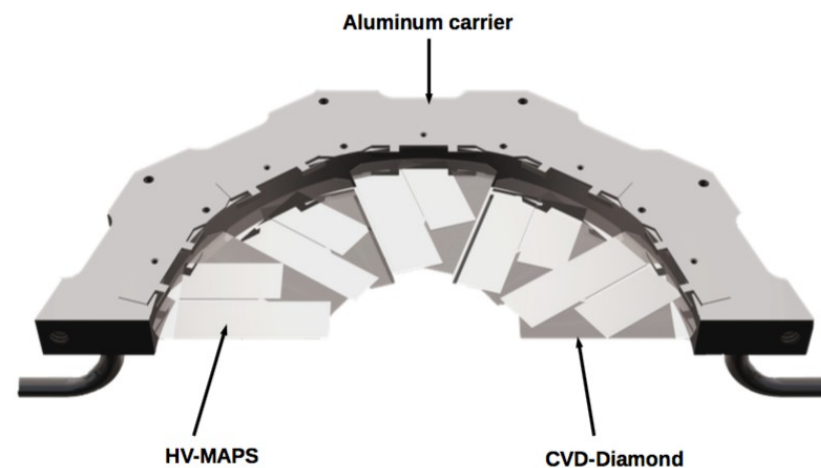
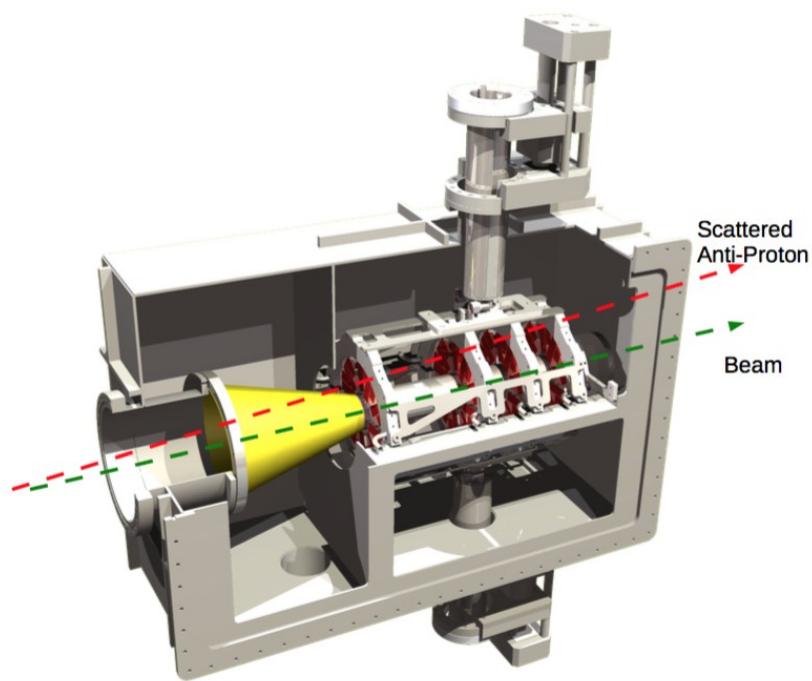
- Panda Tracking system
 - Several gas-based detectors
 - Double-sided silicon strips for the Micro-Vertex-Detector
 - radiation hardness for hole collection already marginal (CMOS too late)?
 - Luminosity Monitor expected to use HV-MAPS
 - MuPix type, identical to $\mu 3e$ chip
 - → see Heiko Augustin's talk



Tobias Weber

Nuclear Physics Applications

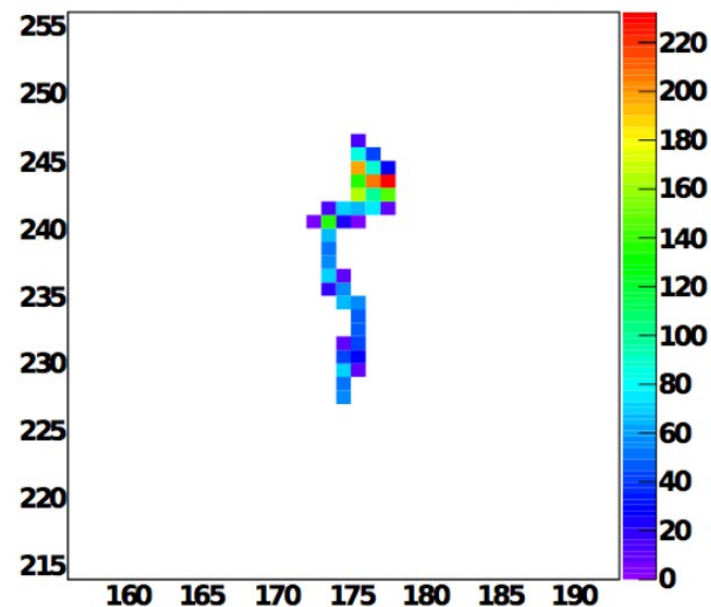
- Panda Tracking system
 - basic idea: mount HV-MAPS chips to CVD diamond substrate to provide cooling
 - very thin/low X0 configuration possible
 - HV-CMOS sensors tolerate running at rather high temperatures and with significant ΔT across the sensor



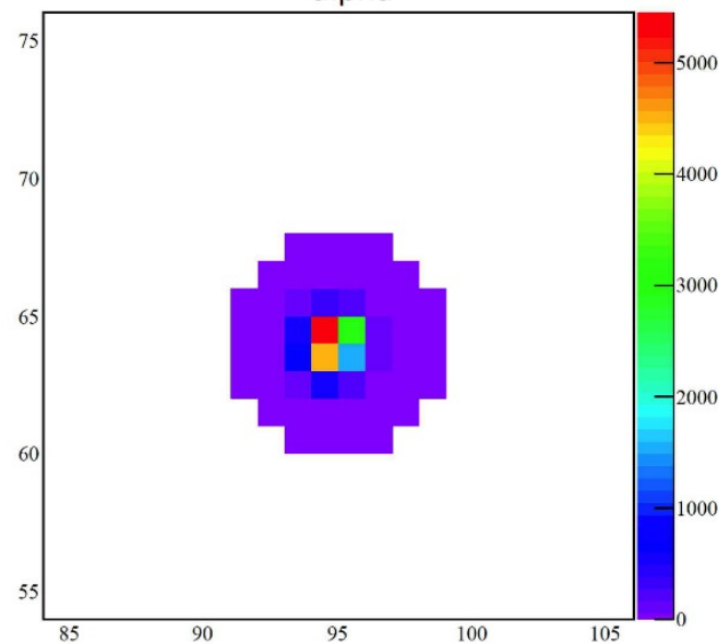
Further “Nuclear” Applications

- Most nuclear physics applications are based on detection/spectroscopy of gamma rays
 - not ideal
- But Particle ID is possible
- Potential instrumentation for “nuclear” things:
 - contamination monitors: large areas, currently ionisation chambers or scintillators for beta (and alpha) detection
 - tritium detection: low-energy beta (14 keV), short range

single electron

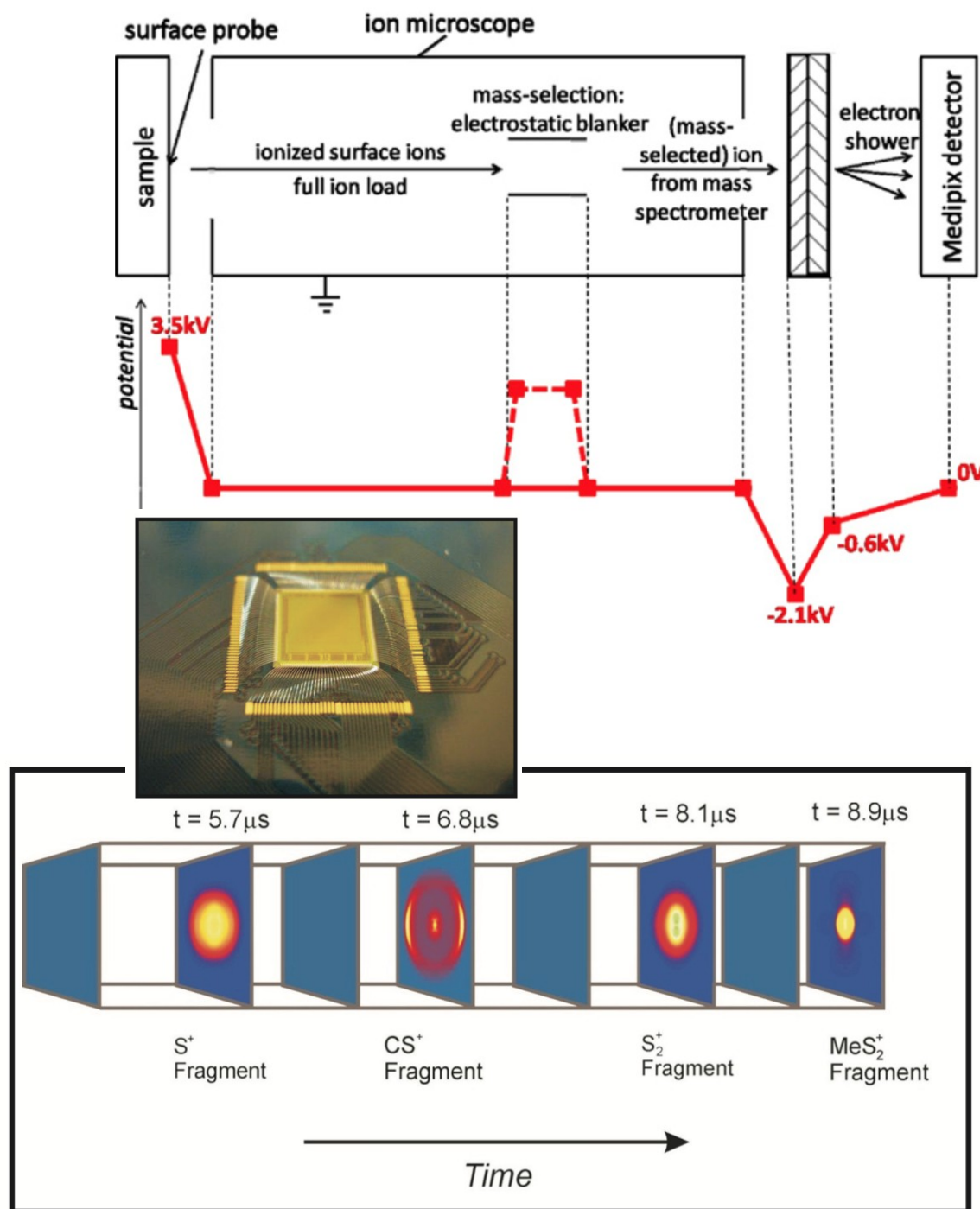


alpha



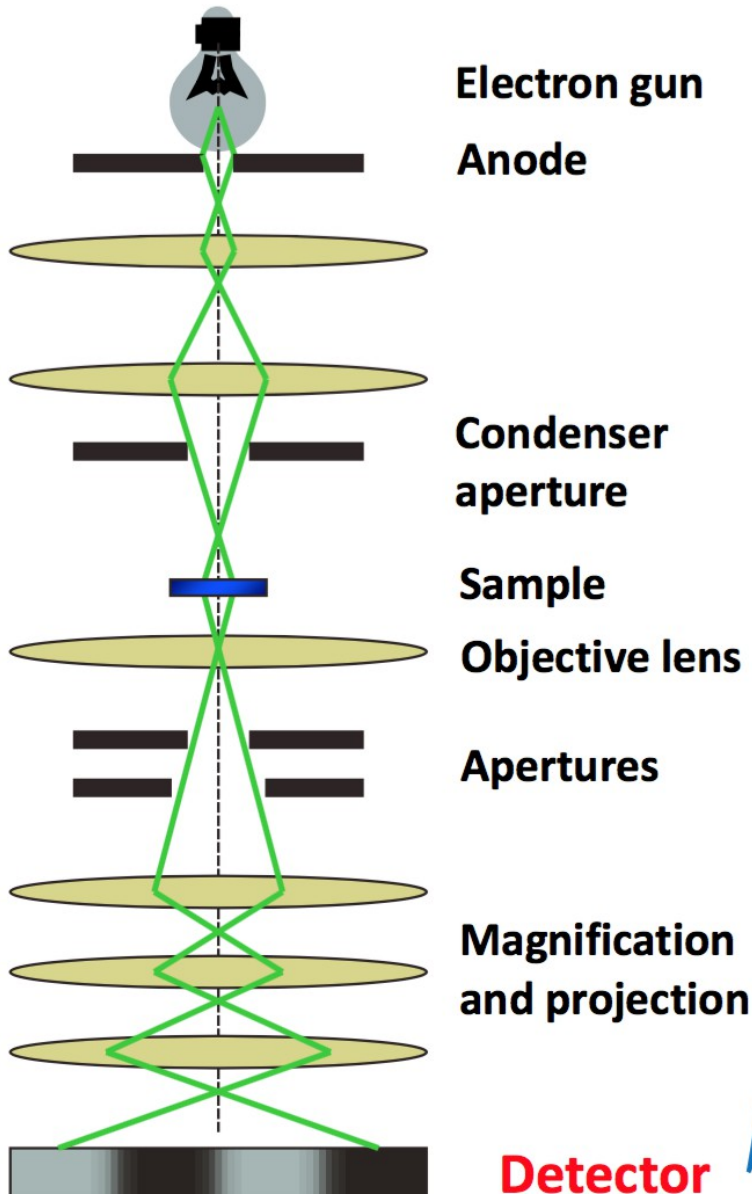
Mass spectroscopy

- Two main methods: magnetic analysis or ion time-of-flight
- Up to now other detector types in use, e.g. Multi Channel Plates for electron amplification followed by a suitable sensor, e.g. a pixel readout chip
- PImMS chip designed for detecting light from MCP/Phosphor layer
 - TOF-compatible
- Direct ion detection possible and could be advantageous, but ion range in detector limited, beware of dead surface layers



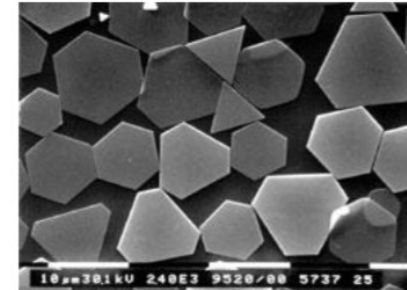
Electron Microscopy

Imaging in Transmission Electron Microscopy



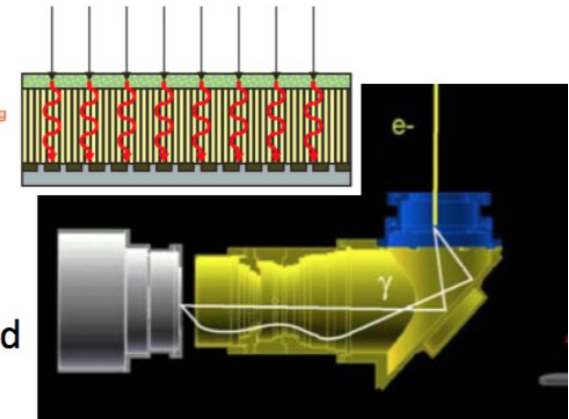
Film

- Large area
- High granularity
- Slow, no dynamic imaging



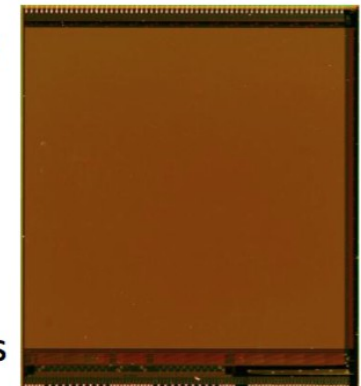
Optically Coupled CCDs

- Limited PSF due to scintillator and backscattering from optics



Direct Semiconductor Pixel Detectors

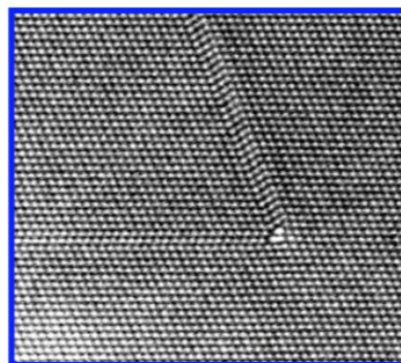
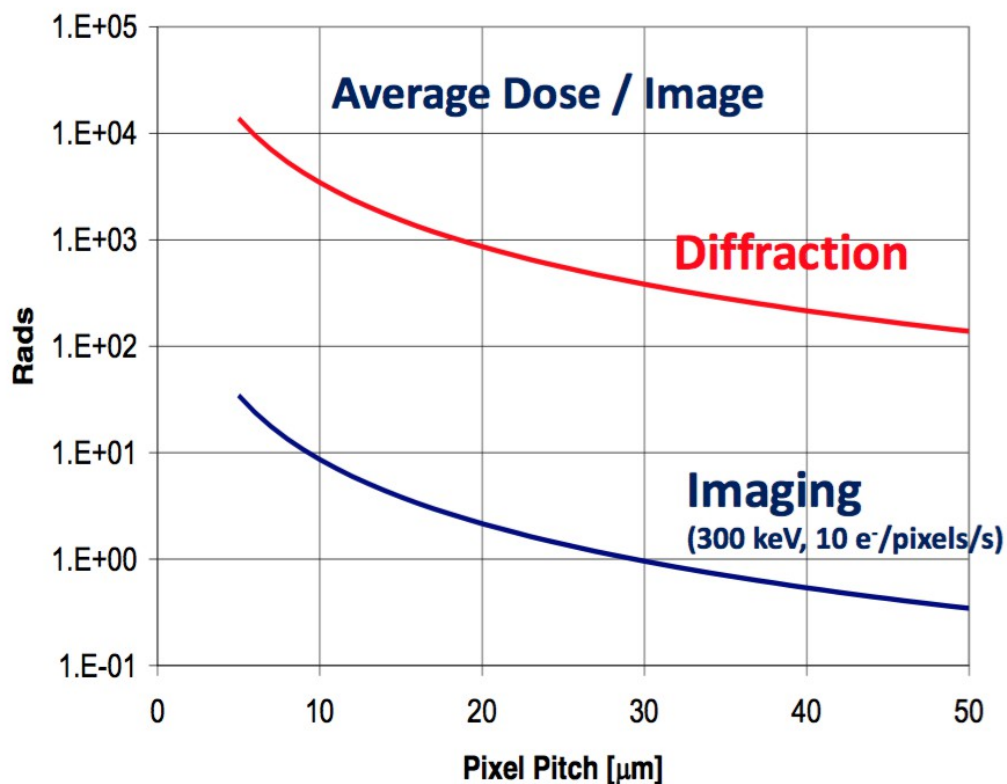
- High PSF and DQE from direct detection
- High speed readout
- Data processing capabilities



Devis Contarato

Electron Microscopy

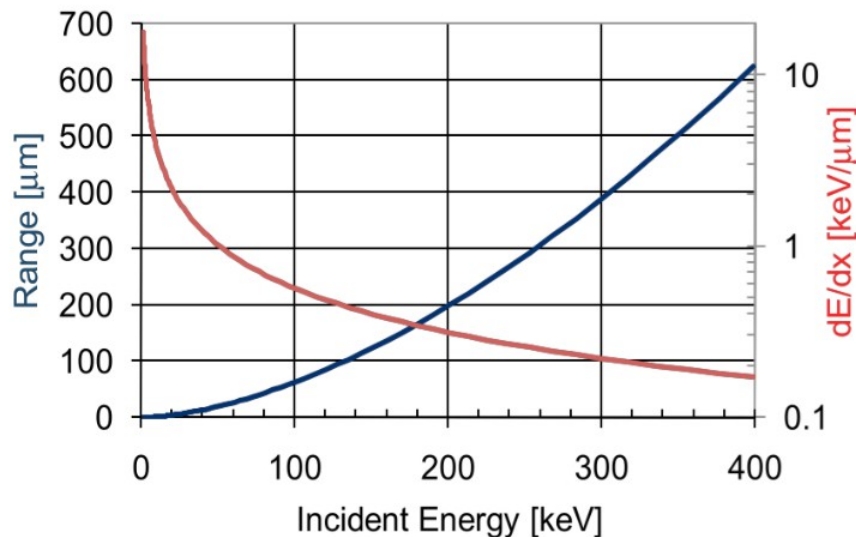
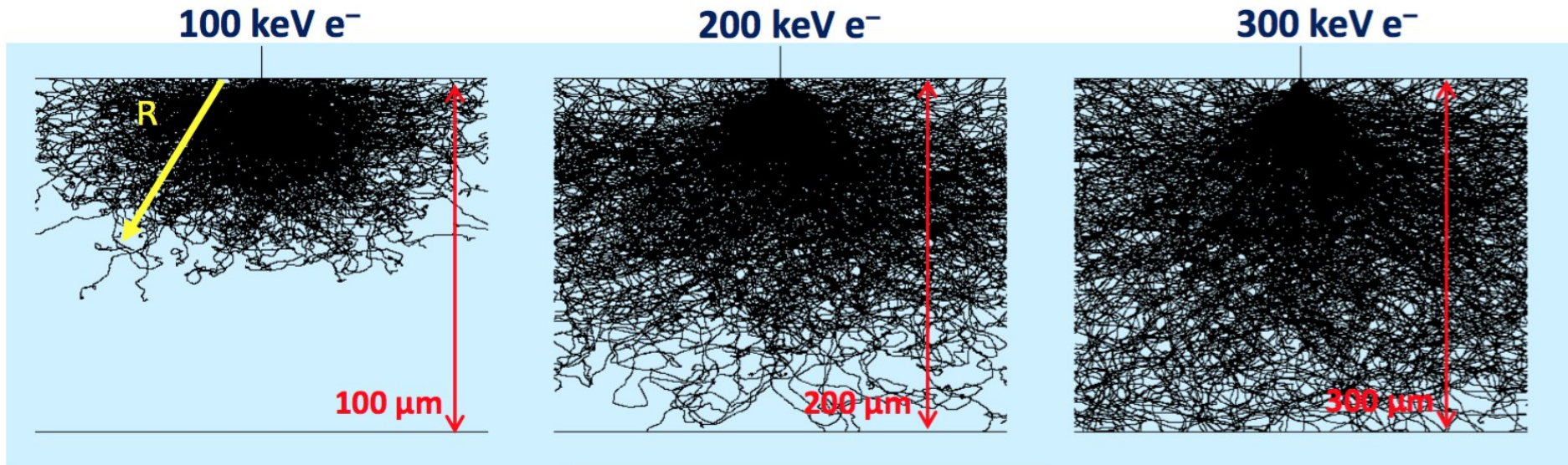
Detector R&D Drivers: Radiation Hardness



- **Imaging mode:** O(1-10 Mrad) ionising dose expected for typical yearly usage (low dose conditions)
- **Diffraction mode:** very high doses localized in bright spots
- Radiation tolerance requirements comparable or worse than High Energy Physics applications
→ leverage extensive R&D on radiation tolerant design of sensors and readout electronics

Electron Microscopy

Detector R&D Drivers: Multiple Scattering



- Energies of interest to TEM: 80-400 keV
- Electron range R [μm] $\sim E$ [keV]
- Energy loss $dE/dx \propto 1/E$
- Need for a thin sensitive layer to minimize scattering contribution to Point Spread Function

Electron Microscopy

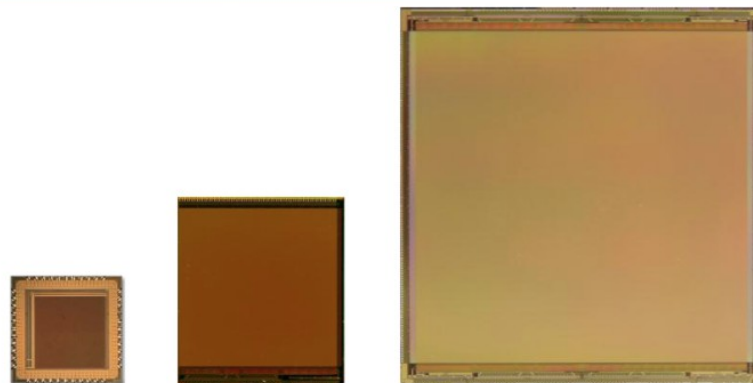
Three Generations of CMOS APS for TEM Imaging

1st Generation (2008-2009)0.35 μm CMOS \rightarrow ams C3509.5 μm pixels

1 & 4 Mpixels

400 fps \rightarrow 400 Mpixels/s

Imagers for the TEAM Project at NCEM

**2nd Generation (2009-2011)**0.18 μm CMOS5 μm pixels

16 MPixels

400 fps \rightarrow 6400 Mpixels/s

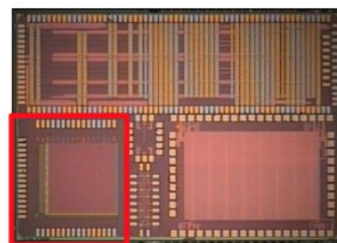
Commercialized by Gatan, Inc.

<http://www.gatan.com/K2/>**3rd Generation (2011 – in progress)**

65 nm CMOS

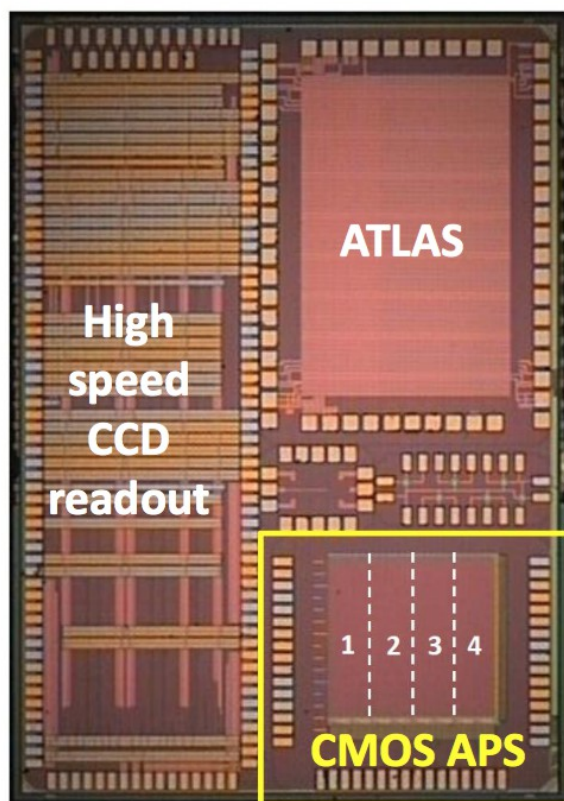
2.5 μm pixels

Prototype sensor under evaluation



Devis Contarato

Electron Microscopy

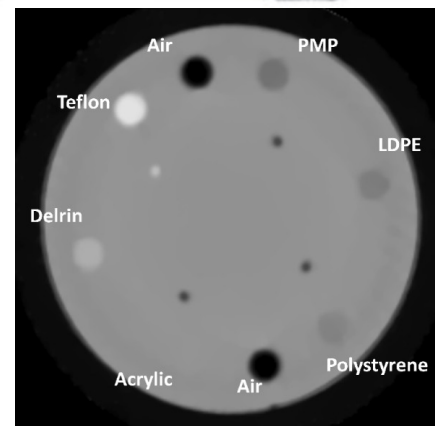
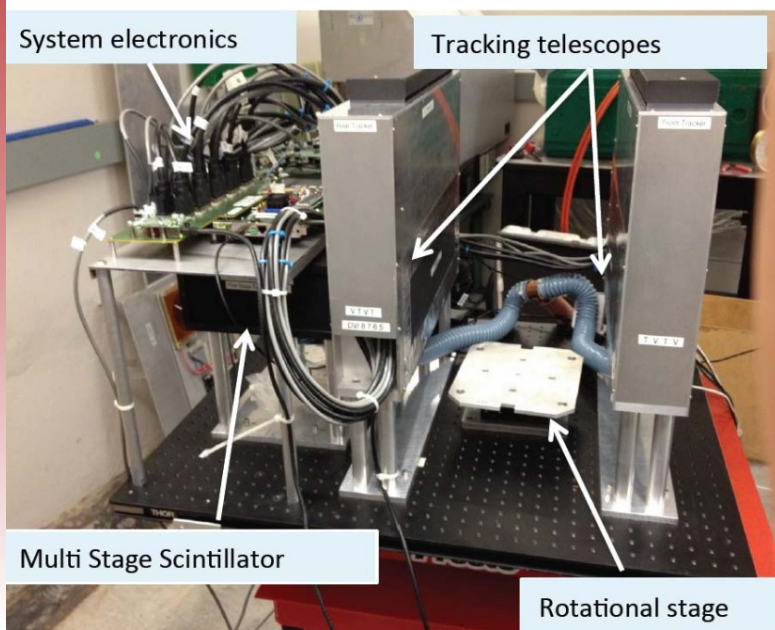
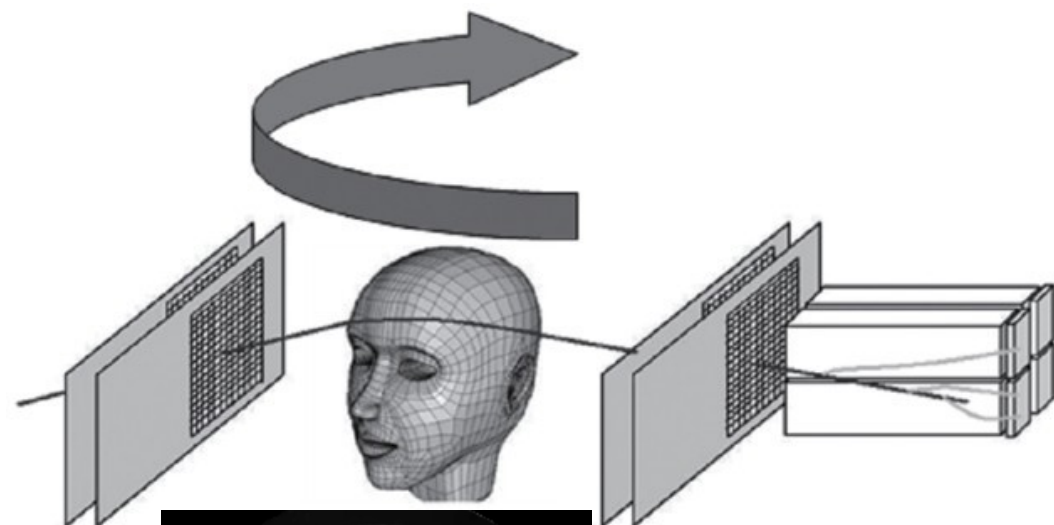
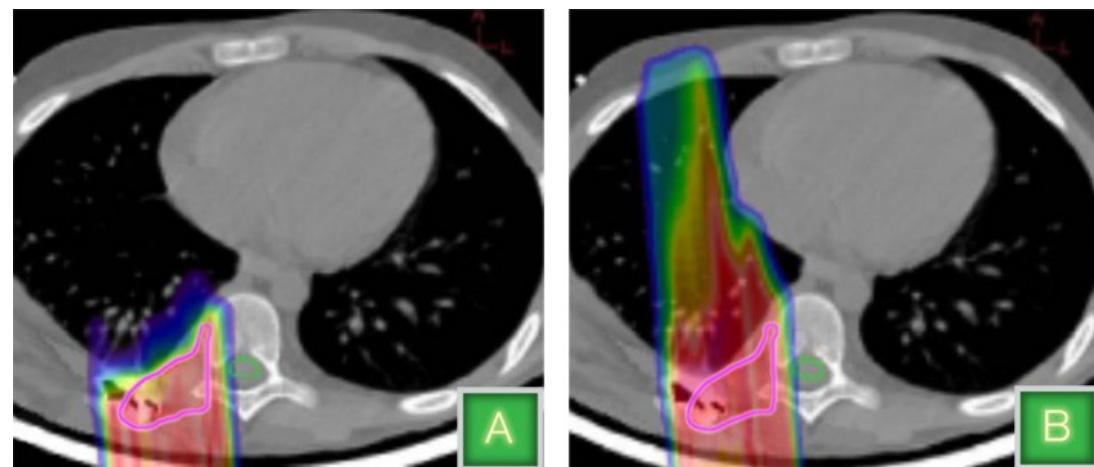
3rd Generation Development in 65 nm CMOS

- Commercial 65 nm CMOS mixed-signal/logic process (not imaging process)
- Submission shared with BES and HEP projects (2011)
- CMOS APS: 400×400 pixels, 2.5 μm pitch, 1×1 mm^2 active area
- Implement 4 sectors with various pixel layouts

	Sector 1	Sector 2	Sector 3	Sector 4
Diode layout	TEAM-like	TEAM-like	TEAM-like	New “pseudo-pinned”
Gate Leakage Compensation	Yes	Yes	Yes	No
MOSFET layout	Enclosed Layout	Standard	Standard	Standard
MOSFET V_{th}	Standard (0.3 V)	Standard (0.3 V)	Low (0.2 V)	Low (0.2 V)

Medical applications: pCT

- Proton Computed Tomography is a CT method specifically suitable for proton/hadron therapy
 - standard CT measures electron densities, not mass densities required for precise hadron treatment planning
 - Measure the scattering along each track followed by an energy measurement

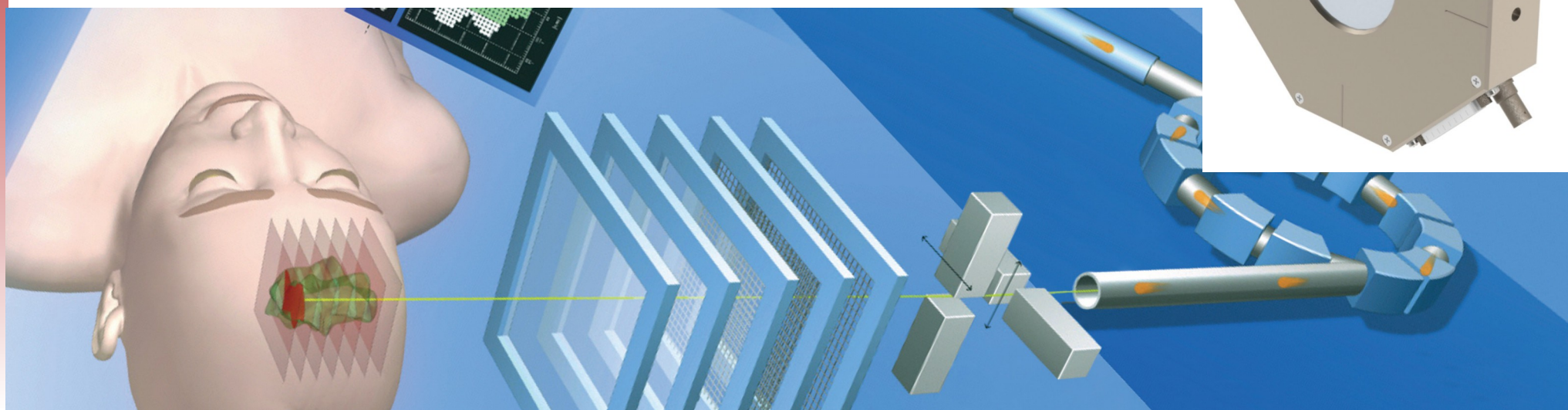
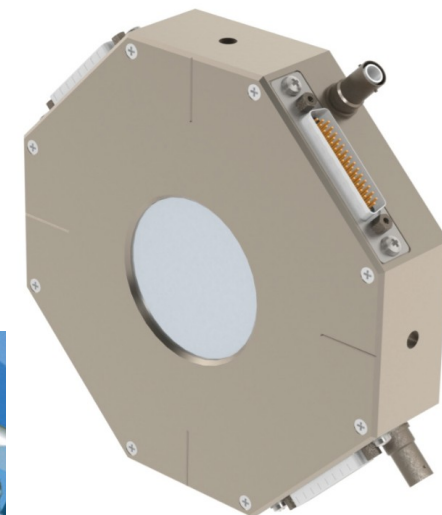
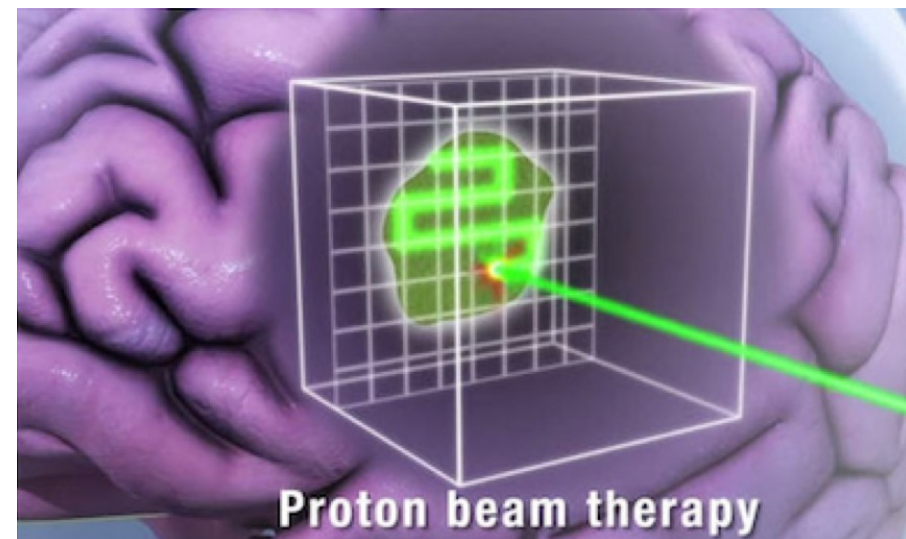


Medical applications: pCT

- Tracking sensors up to now
 - Silicon strip sensors
 - Fibre Trackers
 - GEMs
- CMOS detectors might be interesting candidates, in particular thanks to being able to being operated thin and giving both coordinates at the same time

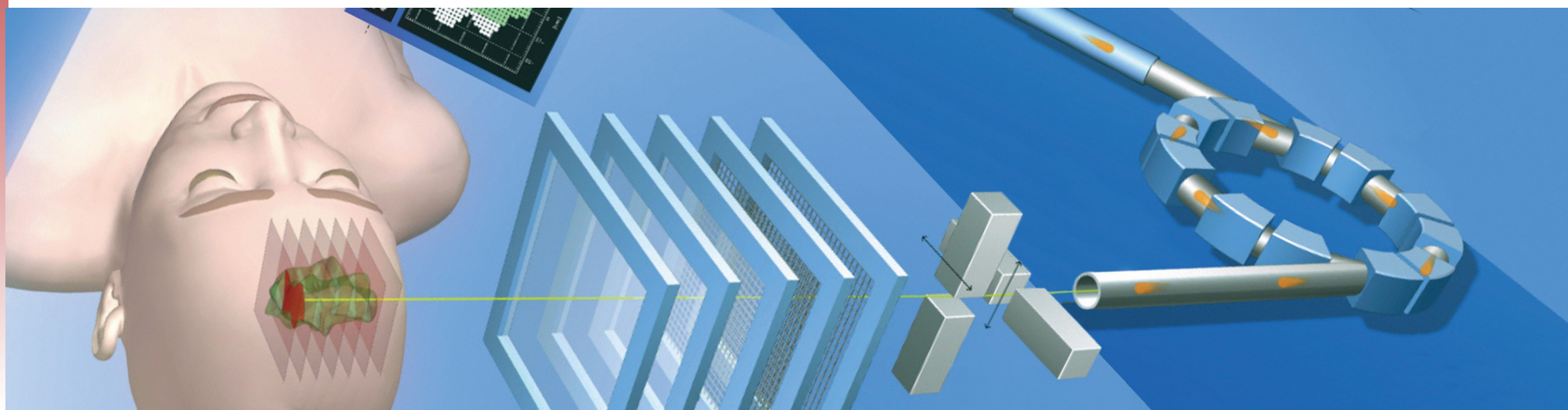
Medical applications: particle therapy

- Particle Cancer Therapy requires stringent QA
 - regular (daily) control measurements of beam steering and energy calibrations
 - beam monitoring during treatment including feedback to beam steering
- Up to now done with stack of ionisation chambers
 - not individual particles, but mean current is measured
 - material budget important



Medical applications: particle therapy

- CMOS detectors very good candidates for this application
 - radiation hard (1e9 protons/s with 1mm beam diameter)
 - high particle rates (ditto)
 - good resolution (currently: 500 μm beam mean)
 - fast readout (currently: 250 μm , is limiting scan speed)
 - low material budget (currently: 500 μm water equivalent \rightarrow thinned devices)
 - even individual particle tracking might be an option
- Mobile detectors could also be applied to skin over entry ports or even body cavities
 - direct measurement of particle tracks, comparison to treatment planning



Conclusions

- CMOS sensors applicable to charged particle detection also outside of HEP tracker applications
- Many requirements rather relaxed compared to LHC environments
 - recycling of architectures generally possible
 - potential issues:
 - high NRE costs for reticule-sized detectors
 - design towards versatility?
 - Large areas required, efficiency gaps sometimes an issue
 - very thin sensors with overlap?
 - stitching?
- Major issues:
 - (lack of) chip designers in several communities
 - comparatively high initial investment (both monetary and know-how wise) compared to established technologies